Technical Digest for International conference

Opto-Electronic Integrated circuit


InP MOVPE growth


InP DFB lasers, InP strained MQW lasers


6. N. Otsuka, M. Kito, Y. Mori, M. Ishino, and Y. Matsui, "New structure by selective regrowth in MQW laser diodes performed by low pressure MOVPE", in Proc. 7th International Conference on Metalorganic Vapor Phase Epitaxy (Yokohama, Japan, 1994) Paper P3-2, pp. 268-269.


8. N. Otsuka, M. Kito, M. Ishino, and Y. Matsui, "1.5 μm strained-layer MQW-DFB lasers with low chirp and low distortion characteristics", in Tech Digest of 10th International Conference on Integrated Optics and Optical Fiber Communication '95 (Hong Kong, 1995) Paper FB2-6, pp. 50-51.


InP Self-limiting Etching


InP Molecular Layer Epitaxy


GaN Blue Laser Diodes and Ultraviolet Light-Emitting Diodes

23. N. Otsuka, A. Tsujimura, Y. Hasegawa, G. Sugahara, M. Kume, and Y. Ban “339 nm Deep-UV Emission from Al<sub>0.13</sub>Ga<sub>0.87</sub>N/Al<sub>0.10</sub>Ga<sub>0.90</sub>N Double Heterostructure Light-Emitting Diode on Sapphire Substrate”, in Tech Digest of International Workshop on Nitride Semiconductors (IWN2000) (Nagoya, Japan, 2000) paper WM1-2, pp. 114.


GaN Power devices, GaN MMICs


50. Yasufumi Kawai; Shuichi Nagai; Osamu Tabata; Hideaki Fujiwara; Noboru Negoro; Hiroaki Ueno; Masahiro Ishida; Nobuyuki Otuska “An isolated DC power supply free compact GaN inverter module”, 2015 IEEE 11th International Conference on Power Electronics and Drive Systems, pp. 84-88, 2015.